

AMENDMENT UNDER 37 C.F.R. § 1.111  
U.S. Appln. No. 10/002,177

**AMENDMENTS TO THE SPECIFICATION**

**Page 6, paragraph 2:**

However, these prior art substrate rotating ~~mechanism~~ mechanisms have the following drawbacks:

**Page 7, paragraph 4:**

(5) When the substrate rotating mechanism rotates the substrate by injecting a gas toward the reverse side of the substrate, a foreign object, such as a deposit caused by a part of reaction products, is subject to be whirled up at the substrate tray and its periphery by the injection of the gas, resulting in a deposit or adhesion of the foreign object at the reverse side and the front side of the substrate.

**Page 15, paragraph 2:**

Further, in the aforementioned film-forming device with a substrate rotating mechanism, the certain film-forming process may be a thin-film growth by Metal Organic Chemical Vapor Deposition (MOCVD) ~~(see FIG. 8)~~.